U.S. Department of Commerce, Patent and Trademark Office	Atty Docket No.	Application No.
	M-10096 US	09/832,933
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant(s)	
(Use several sheets if necessary)	Lifeng Wu et al.	
	Filing Date	Group
	April 11, 2001	2123

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
TS	AA	5,533,197	Jul. 2, 1996	Moran et al.			
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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